Document Number: GMAH0070-1 Production Datasheet V1.0

DC-7GHz, 1W, 28V GaN Fully matched PA Module

Description

The GMAH0070-1 is a 1-watt ,single stage integrated Power Amplifier Module, designed for broad band applications, with frequencies from DC to 7GHz. The module is 50 Ω input/output matched and requires minimal external components.

The module implements distributed power amplifier in form of multi chips, housed in cost effective plastic open cavity package, offers a much lower cost than traditional MMIC solutions.



Vds=28V, Idq=10mA, CW

Parameter	30MHz	0.5GHz	1.0GHz	2.0GHz	3.0GHz	4.0GHz	5.0GHz	6.0GHz	6.9GHz	Units
Gain	11.9	12.4	11.9	11.9	12.0	11.4	12.0	12.4	17.9	dB
Psat	2.0	2. 5	2.4	2. 3	2.0	2.1	2.4	2.0	1.5	W
Gain@Psat	8.9	9.4	8.9	8.9	9.0	8.4	9.0	9.4	14.9	dB
Eff@Psat	42	43	40	38	34	32	35	30	37	%

Product Features

• Operating Frequency Range: DC-7GHz

• Operating Drain Voltage: +28 V

50 Ω Input/Output
 P3dB: ≥30 dBm

• Small signal gain:>11dB, Power gain:>8dB

• Minimum efficiency:>25%

• 6x10 mm Surface Mount Package

• Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

Applications

• Ultra Broadband Amplifiers

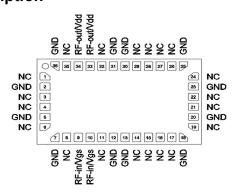
• Fiber Drivers

• Test Instrumentation

• EMC Amplifier Drivers

• 2-way Radios

Pin Configuration and Description



Top View



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Document Number: GMAH0070-1 Production Datasheet V1.0

Pin No.	Symbol	Description		
33,34	RFout/Vdd	Transistor 1, Drain Bias & RF Output		
9,10	RFin/Vgs	Transistor 1, RF Input &Gate Bias		
Others	NC	No connection		
2,5,7,12, 13,18,20,23,25, 30, 31,36 Package Base	GND	DC/RF Ground. Must be soldered to EVB ground plane over array of vias for thermal and RF performance. Solder voids under Pkg Base will result in excessive junction temperatures causing permanent damage.		

Rating	Symbol	Value	Unit
DrainSource Voltage	V _{DSS}	150	Vdc
GateSource Voltage	V_{GS}	-10 to +2	Vdc
Operating Voltage	V_{DD}	+36	Vdc
Storage Temperature Range	Tstg	-65 to +150	°C
Case Operating Temperature	Tc	+150	°C
Operating Junction Temperature	T,	+225	°C

Table 1. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	Rejc	0	°C/W
T _C = 87°C, T _J =175°C, DC test	Keac	O	-0/00

Table 3. Electrical Characteristics

Parameter	Condition	Min	Тур	Max	Unit	
Frequency Range		30		7000	MHz	
Power Gain @ Psat		8			dB	
P _{SAT}		30			dBm	
Drain Efficiency @ P _{SAT} 30 %						
Unless otherwise noted: TA = 25°C, Vnn =28 V, Pulse Width=100 us. Duty cycle=10%						

Load Mismatch of per Section (On Test Fixture, 50 ohm system): $V_{DD} = 28 \text{ V}$, $I_{DQ} = 10 \text{ mA}$, f = 3.5 GHz

VSWR 10:1 at P3dB pulse CW Output Power	No Device Degradation
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Document Number: GMAH0070-1 Production Datasheet V1.0

Reference Circuit of Test Fixture Assembly Diagram

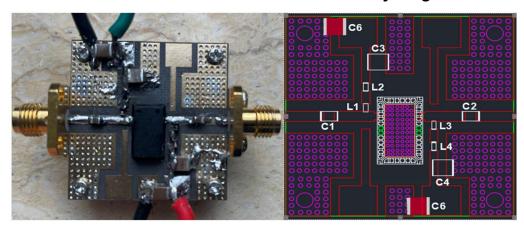
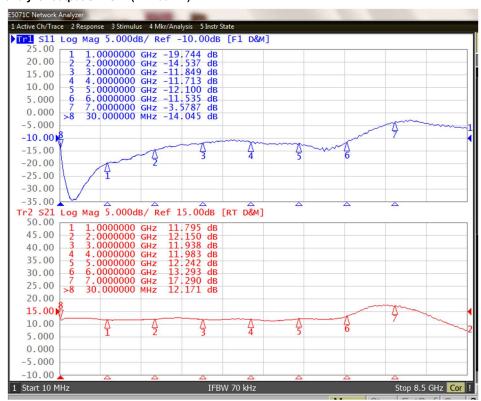


Figure 1. Test Circuit Component Layout

		Part NO.←	Vendor←
C <u>1, C</u> 2←	1uF Chip Capacitor←	42	ATC←
C3, C4€	390pF Chip Capacitor↔	43	ATC€
C5, C6←	10uF 100V chip Capacitor⊖	43	43
L1, L3↔	100nH 1000mA Inductor⊖	LQW18CNR10K00D←	Coilcraft↩
L2, L5↔	470nH 500mA Inductor⊖	LQW18CNR47J00D←	Coilcraft<
PCB←	R05880, 20mil, er=2. 2€	43	MTL←

TYPICAL CHARACTERISTICS

Figure 2. Network analyzer output S11/S21 (Pin=0dBm)

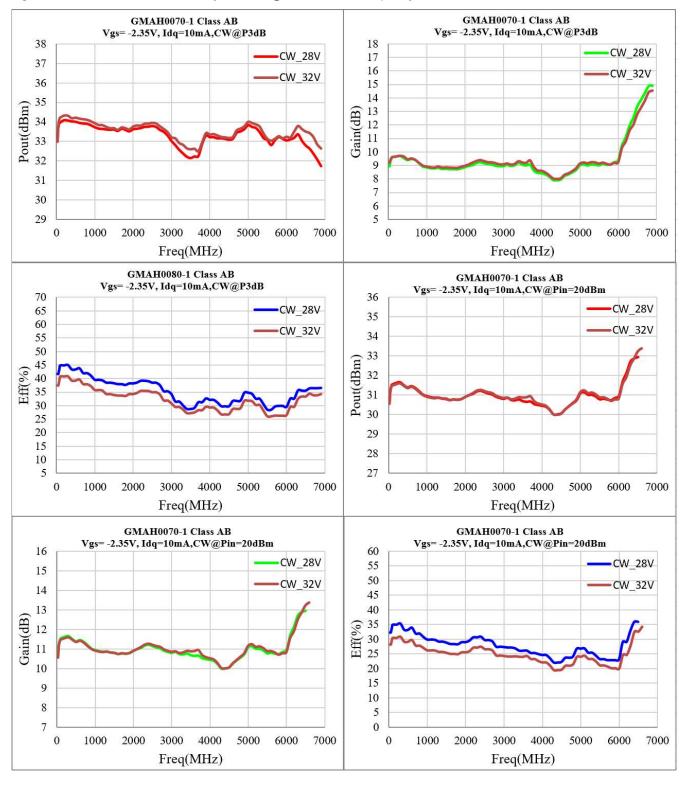




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Document Number: GMAH0070-1 Production Datasheet V1.0

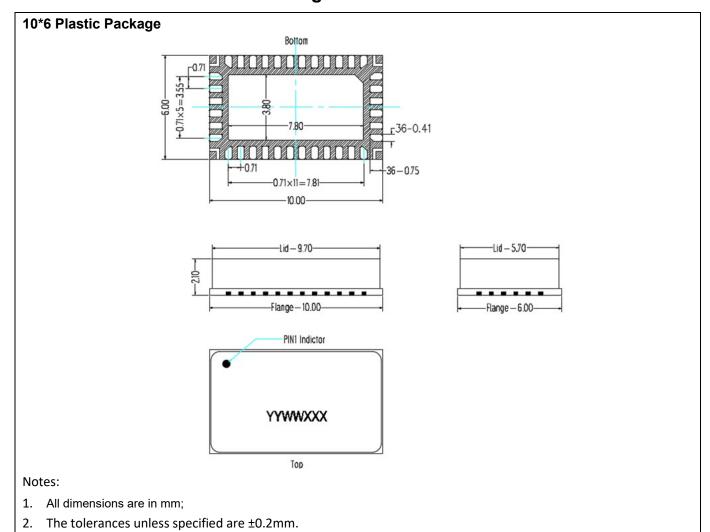
Figure. Psat, Power Gain and, efficiency and Pout @Pin=20dBm vs. Frequency



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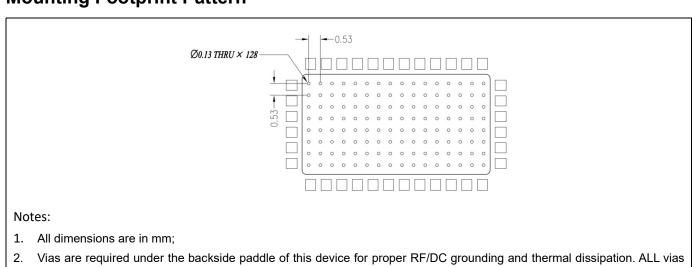
Document Number: GMAH0070-1 Production Datasheet V1.0

Package Dimensions



Mounting Footprint Pattern

are PTH to ground.



Document Number: GMAH0070-1 Production Datasheet V1.0

Revision history

Table 6. Document revision history

Date	Revision	Datasheet Status
2022/12/9	Rev 1.0	Production Datasheet

Application data based on ZHH-21-12

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